Semiconductors

High-reliability discrete products
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2N4913-2N4915

NPN SILICON MEDIUM POWER TRANSISTORS

FEATURES

- Available as “HR” (high reliability) screened per MIL-PRF-19500, JANTX level. Add “HR” suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding “-PBF” suffix.

MAXIMUM RATINGS

Rating	Symbol	2N4913	2N4914	2N4915	Unit
Collector-emitter voltage	V_{CEO}	40	60	80	Vdc
Collector-base voltage	V_{CB}	40	60	80	Vdc
Emitter-base voltage	V_{EB}	5.0			Vdc
Collector current – continuous	I_C	5.0			Adc
Base current	I_B	1.0			Adc
Total device dissipation T_C = 25°C **Derate above 25°C**	P_D	87.5 0.5			Watts W/°C
Operating and storage junction temperature range	T_J, T_{stg}	-65 to +200			°C
Thermal resistance, junction to case	Θ_{JC}	2.0			°C/W

ELECTRICAL CHARACTERSITICS (T_A = 25°C unless otherwise specified)

Characteristics		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector emitter sustaining voltage (I_C = 0.2Adc, I_B = 0)	2N4913 2N4914 2N4915	$B_{VCEO(sus)}$	40 60 80	- - -	Vdc
Collector cutoff current (V_{CE} = Rated V_{CEO}, I_B = 0)		I_{CEO}	-	1.0	mAdc
Collector cutoff current (V_{CE} = Rated V_{CEO}, $V_{BE(off)}$ = 1.5Vdc) (V_{CE} = Rated V_{CEO}, $V_{BE(off)}$ = 1.5Vdc, T_C = 150°C)		I_{CEX}	- -	1.0 2.0	mAdc
Collector cutoff current (V_{CB} = Rated V_{CB}, I_E = 0)		I_{CBO}	-	1.0	mAdc
Emitter cutoff current (V_{EB} = 5.0Vdc, I_C = 0)		I_{EBO}	-	1.0	mAdc
ON CHARACTERISTICS					
DC current gain (1) (I_C = 2.5Adc, V_{CE} = 2.0Vdc) (I_C = 5.0Adc, V_{CE} = 2.0Vdc)		h_{FE}	25 7.0	100 -	-
Collector emitter saturation voltage (I_C = 2.5Adc, I_B = 250mAdc) (I_C =5.0Adc, I_B = 1.0Adc)		$V_{CE(sat)}$	- -	1.0 1.5	Vdc
Base emitter saturation voltage (I_C = 2.5Adc, V_{CE} = 2.0Adc)		$V_{BE(sat)}$	-	1.4	Vdc
SMALL SIGNAL CHARACTERISTICS					
Current gain - bandwidth product (I_C = 1.0Adc, V_{CE} = 10Vdc, f = 1.0MHz)		f_T	4.0	-	MHz

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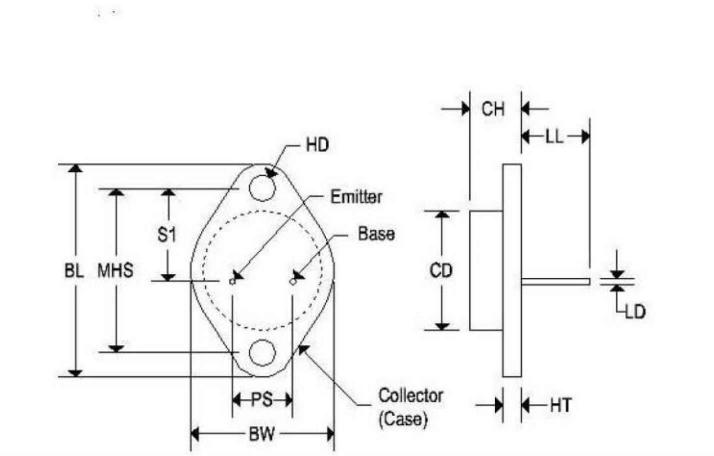
ELECTRICAL CHARACTERSITICS (T_A = 25°C unless otherwise specified)

Characteristics	Symbol	Min	Max	Unit
Small signal current gain (I_C = 500mAdc, V_{CE} = 10Vdc, f = 1.0kHz)	h_{fe}	20	-	-

MECHANICAL CHARACTERISTICS

Case	TO-3
Marking	Alpha-numeric
Polarity	See below



	TO-3			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	-	0.875	-	22.220
CH	0.250	0.380	6.860	9.650
HT	0.060	0.135	1.520	3.430
BW	-	1.050	-	26.670
HD	0.131	0.188	3.330	4.780
LD	0.038	0.043	0.970	1.090
LL	0.312	0.500	7.920	12.700
BL	1.550 REF		39.370 REF	
MHS	1.177	1.197	29.900	30.400
PS	0.420	0.440	10.670	11.180
S1	0.655	0.675	16.640	17.150

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FIGURE 1 — NORMALIZED DC CURRENT GAIN

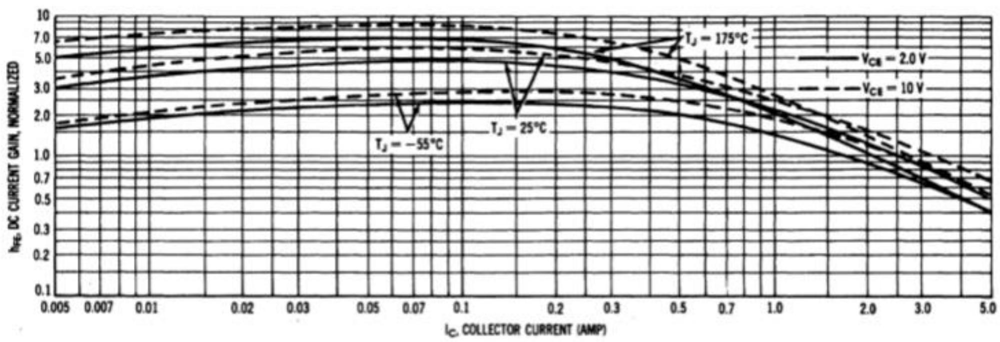


FIGURE 2 — COLLECTOR SATURATION REGION

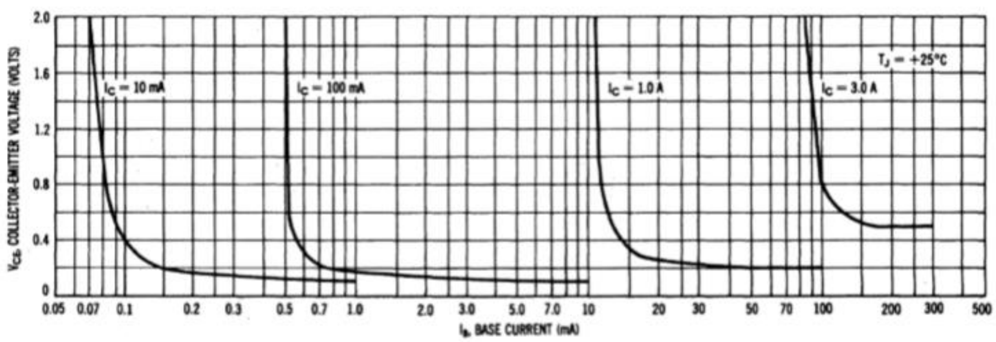


FIGURE 3 — "ON" VOLTAGES

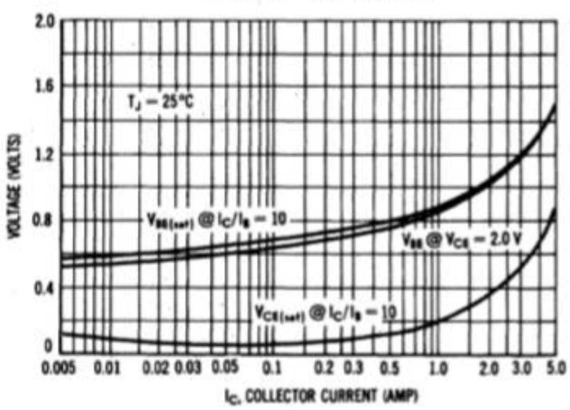
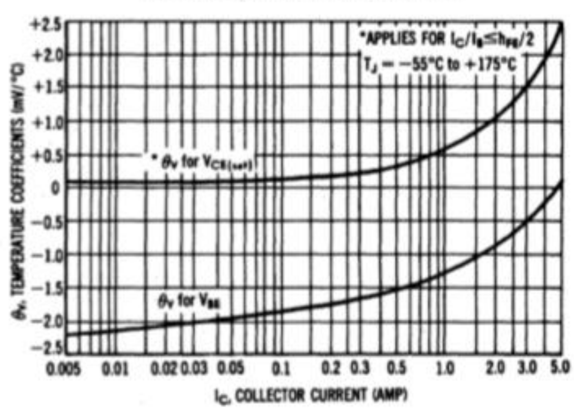


FIGURE 4 — TEMPERATURE COEFFICIENTS



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TYPICAL "OFF" REGION CHARACTERISTICS

FIGURE 5 — CUT-OFF REGION

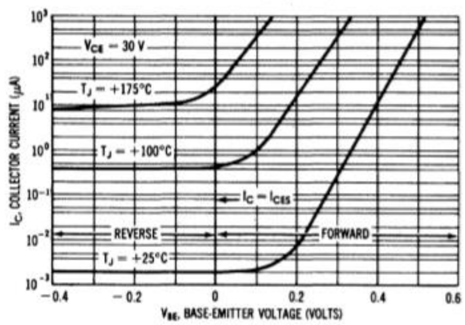

FIGURE 6 — EFFECTS OF BASE-EMITTER RESISTANCE

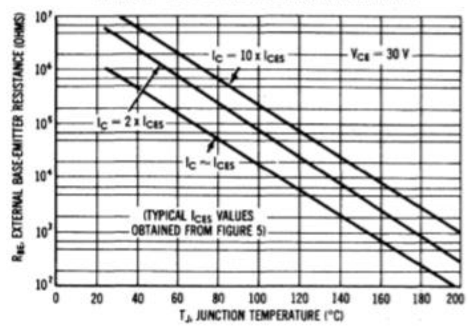

FIGURE 7 — SWITCHING TIME EQUIVALENT CIRCUIT

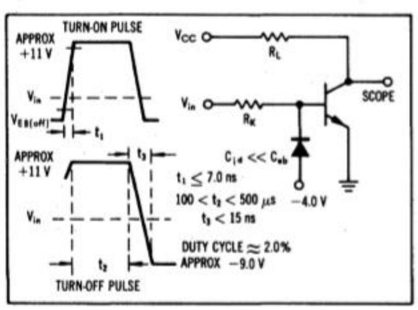

FIGURE 8 — CAPACITANCE

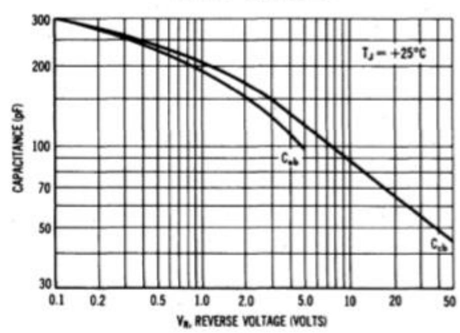

FIGURE 9 — TURN-ON TIME

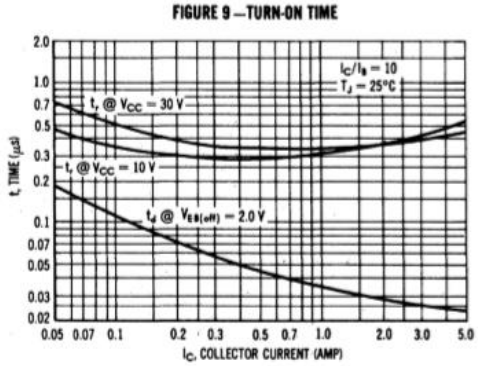

FIGURE 10 — TURN-OFF TIME

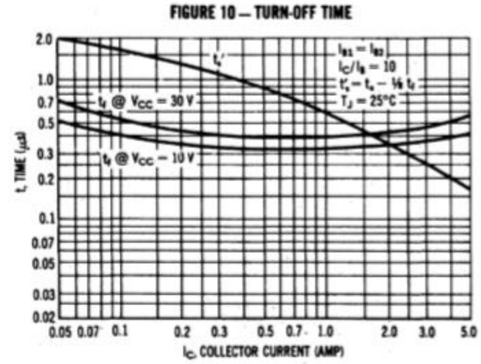

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FIGURE 11 — ACTIVE-REGION SAFE OPERATING AREAS

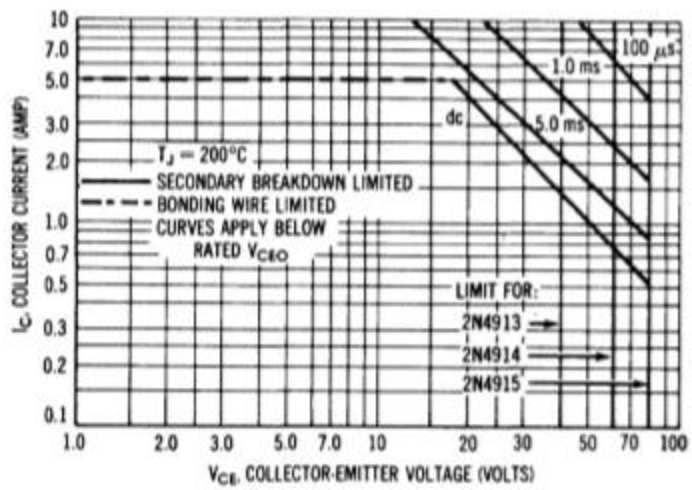
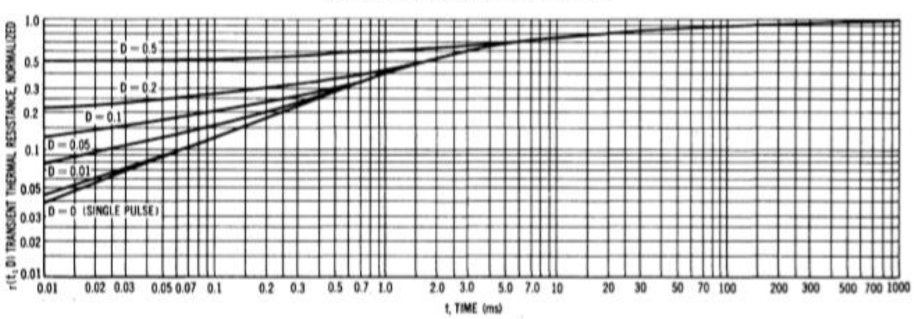
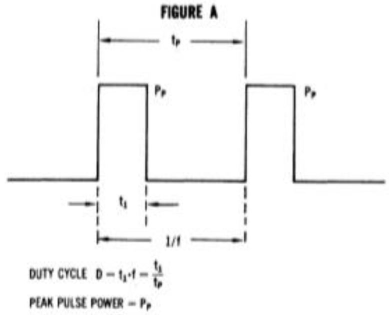


FIGURE 12 — TRANSIENT THERMAL RESISTANCE



DESIGN NOTE: USE OF TRANSIENT THERMAL RESISTANCE DATA

FIGURE A



A train of periodical power pulses can be represented by the model as shown in Figure A. Using the model and the device thermal response, the normalized effective transient thermal resistance of Figure 12 was calculated for various duty cycles.

To find $\theta_{JC}(t)$, multiply the value obtained from Figure 12 by the steady state value θ_{JC}.

Example:

The 2N4913 is dissipating 100 watts under the following conditions: $t_1 = 0.1$ ms, $t_P = 0.5$ ms. $(D = 0.2)$

Using Figure 12, at a pulse width of 0.1 ms and D = 0.2, the reading of r (t_1, D) is 0.28.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_P \times \theta_{JC} = 0.28 \times 100 \times 2.0 = 56°C$$